## Advanced Piezoelectric crystals of La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub> Family D.V. Roshchupkin, O.A. Plotitcyna Institute of Microelectronics Technology and High-Purity Materials Russian Academy of Sciences

## Plan of presentation

- 1. Advanced piezoelectric crystals for acoustoelectronics
- 2. Crystal structure perfection
- 3. Independent piezoelectric strain coefficients ( $d_{11}$ ,  $d_{14}$ ) in La<sub>3</sub>Ga<sub>5.3</sub>Ta<sub>0.5</sub>Al<sub>0.2</sub>O<sub>14</sub> and Ca<sub>3</sub>TaGa<sub>3</sub>Si<sub>2</sub>O<sub>14</sub> crystals
- 4. QCM Microbalance based on LGTA crystal
- 5. High temperature wireless sensor based on surface acoustic waves resonators (-90°C ÷ 1000°C, LGS: La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub>)
- 6. Fast X-Ray beam chopper
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- 8. Ordering  $Ca_3$ Ta $Ga_3Si_2O_{14}$  crystal
- 9. Non-ordering  $La_3Ga_{5.3}Ta_{0.5}AI_{0.2}O_{14}$  crystal
- 10. Investigation of surface and pseudo-surface acoustic waves excitation and propagation in La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub> crystal

## 1. Advanced piezoelectric crystals for acoustoelectronics

Crystals of La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub> (LGS, langasite) family, point group symmetry 32



4" non-ordering La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub> crystal grown along axis {001}



3" non-ordering La<sub>3</sub>Ga<sub>5.5</sub>Ta<sub>0.5</sub>O<sub>14</sub> crystal grown along axis {001}



3" ordering  $Ca_3TaGa_3Si_2O_{14}$  crystal grown along axis {110}



3" non-ordering La<sub>3</sub>Ga<sub>5.5</sub>Ta<sub>0.3</sub>Al<sub>0.2</sub>O<sub>14</sub> crystal grown along axis {110}

## 2. Crystal structure perfection





X-ray topographs of LGTA: (a) reflection (003),  $\Theta_B$ =21.901°,  $\lambda$ =1.276 Å; (b) reflection (220),  $\Theta_B$ =17.836°,  $\lambda$ =1.276 Å.

## Measurements of interplanar spacing in LGTA crystal



XRD diffraction spectrum of LGTA crystal

Reflection (hkl)	2Θ, °	d <sub>(<i>hkl)</i>, Å</sub>
(100)	12,2438	7,2203
(001)	16,9112	5,2366
(110)	21,4094	4,1454
(200)	24,8491	3,5788
(111)	27,6327	3,2243
(201)	30,4162	2,9353
(210)	33,1152	2,7020
(002)	34,8404	2,5720
(300)	38,3648	2,3434
(112)	41,3918	2,1788
(202)	43,4344	2,0809
(220)	44,6199	2,0283
(310)	45,8188	1,9780
(221)	47,5304	1,9107
(212)	48,9275	1,8594
(400)	51,2136	1,7816
(302)	52,4413	1,7427
(003)	53,5103	1,7104
(222)	57,4369	1,6025
(321)	59,2362	1,5580
(203)	60,0617	1,5384
(402)	63,6603	1,4600
(500)	65,3007	1,4272
(501)	68,1670	1,3740

*a*=*b*=2*d*<sub>(110)</sub>=8.2908 Å *c*=2*d*<sub>(002)</sub>=5.144 Å

3. Independent piezoelectric strain coefficients ( $d_{11}$ ,  $d_{14}$ ) in La<sub>3</sub>Ga<sub>5.3</sub>Ta<sub>0.5</sub>Al<sub>0.2</sub>O<sub>14</sub> (LGTA) and Ca<sub>3</sub>TaGa<sub>3</sub>Si<sub>2</sub>O<sub>14</sub> (CTGS) crystals Reverse piezoelectric effect :  $\Delta d_i/d_i = d_{ij} \cdot E_j$ 

X-cut of the LGTA crystal, thickness 200 µm



Measurements of  $d_{11}$  in the Bragg diffraction geometry. Reflection (110).  $d_{11}$ =6.45455×10<sup>-12</sup> C/N



Measurements of  $d_{14}$  in the Laue diffraction geometry. Reflection (201).  $d_{14}$ =-5.11735×10<sup>-12</sup> C/N

References	La <sub>3</sub> Ga <sub>5.3</sub> Ta <sub>0.5</sub> Al <sub>0.2</sub> O <sub>14</sub> (LGTA)		Ca <sub>3</sub> TaGa <sub>3</sub> Si <sub>2</sub> O <sub>14</sub> (CTGS)	
	<i>d</i> <sub>11</sub> ×10 <sup>-12</sup> (C/N)	<i>d</i> <sub>14</sub> ×10 <sup>-12</sup> (C/N)	<i>d</i> <sub>11</sub> ×10 <sup>-12</sup> (C/N)	<i>d</i> <sub>14</sub> ×10 <sup>-12</sup> (C/N)
Ref. 1	6.6	-	-	-
Ref. 2	-	-	-4.58	10.43
Ref. 3	6.455	-5.117	3.331	-15.835

- Shujun Zhang, Akira Yoshikawa, Kei Kamada, Eric Frantz, Ru Xia, David W. Snyder, Tsuguo Fukuda, and Thomas R. Shrout, "<u>Growth and characterization of high temperature La<sub>3</sub>Nb<sub>0.5</sub>Ga<sub>5.3</sub>Al<sub>0.2</sub>O<sub>14</sub> (LNGA) and La<sub>3</sub>Ta<sub>0.5</sub>Ga<sub>5.3</sub>Al<sub>0.2</sub>O<sub>14</sub> (LTGA) piezoelectric single crystals," Solid State Comm. **148** 213 (2008).
  </u>
- Xuzhong Shi, Duorong Yuan, Xin Yin, Aijian Wei, and Shiyi Guo, Fapeng Yu, "<u>Crystal growth</u> and dielectric, piezoelectric and elastic properties of Ca<sub>3</sub>TaGa<sub>3</sub>Si<sub>2</sub>O<sub>14</sub> single crystal," Solid State Comm. **142** 173 (2007).
- 3. Dmitry Irzhak and Dmitry Roshchupkin, Piezoelectric strain coefficients in La<sub>3</sub>Ga<sub>5.3</sub>Ta<sub>0.5</sub>Al<sub>0.2</sub>O<sub>14</sub> and Ca<sub>3</sub>TaGa<sub>3</sub>Si<sub>2</sub>O<sub>14</sub> crystals, AIP Advanced (2013).

## 4. QCM Microbalance based on LGTA crystal



Application of QCM Microbalance:

- Control of the thickness of refractory films in industry;
- Control of the thickness of an epitaxial growth films in micro- and nanoelectronics;
- Monitoring of high-temperature processes;
- Control of hydrogen concentration at the Nuclear Power Plant.



LGTA Y-cut, (100), *f*<sub>0</sub>=5.160 МГц



LGTA Y-36°-cut, (101), *f*<sub>0</sub>=4.490 МГц



LGTA Y+36°-cut, (101), *f*<sub>0</sub>=6.230 МГц

## **QCM BAW-resonators**



Amplitude-frequency response



BAW-resonator,  $f_0$ =5.160 MHz



BAW-resonator,  $f_0$ =6.230 MHz







Experimental set-up of X-ray topograph.

5. High temperature wireless sensor based on surface acoustic waves resonators (-90°C  $\div$  1000°C, LGS: La<sub>3</sub>Ga<sub>5</sub>SiO<sub>14</sub>)





Aero-engine



Package: LGS



*Ir*-IDT (Λ=5.948 μm)



Amplitude-frequency response of SAW-resonator



 $2\Theta$ - $\Theta$  Reflectivity of LGS wafer: black line – experiment, blue line - calculation.  $\lambda$ =1.54 Å, CuK<sub>a1</sub> radiation

Structure of LGS wafer

#	Thickness, nm	Roughness, nm	Density, g/cm <sup>3</sup>
Damaged layer 2	1.64	0.41	4.62
Damaged layer 1	2.67	0.32	5.42
Substrate	0.0	0.20	5.67

## Investigation of Ir layer



 $\lambda$ =1.54 Å, CuK<sub>q1</sub> radiation

## Fabrication of SAW-resonator





#### SAW-resonator structure ( $\Lambda$ =5.948 µm)







#### Different types of the SAW resonators (Ir)









Apodized SAW transducer

#### Ordinary SAW transducer

### Structure of Ir electrodes measured by AFM



#### SAW-resonators



Coefficient of metallization 34% *f*=409 MHz, V=2432.732 m/s





Coefficient of metallization 51% *f*=402 MHz, V=2391.096 m/s



## 6. Fast X-Ray beam chopper





 $\Lambda$ =4 µm, W=60× $\Lambda$ =240 µm



SAW delay time line based on the X-cut of CTGS crystal:  $\Lambda$ =4 µm, f=700 MHz

X-ray diffraction by X-cut of CTGS crystal modulated by SAW with wavelength of  $\Lambda$ =4 µm. Reflection (110),  $\Theta_{\rm B}$ =11.008°,  $f_0$ =700 MHz, V=2800 m/s, surface roughness 4.1 Å





Rocking curve, U=2 V



Experimental set-up of a high-frequency X-ray beam chopper

#### HF acoustooptic modulation of synchrotron radiation at BESSY II



7. SAW imaging by Talbot effect at the synchrotron radiation source

Talbot effect  $Z_T=2\Lambda^2/\lambda$ 



Scheme of a double crystal diffractometer. Saggital diffraction geometry.





Acoustically modulated Y-cut of an LGS crystal. Reflection (100),  $\Lambda$ =10 µm,  $\lambda$ =1Å. SAW imaging at BESSY II, optical beamline KMC 2



Y-cut of a CTGS crystal,  $\Lambda$ =50 µm, f=46.373 MHz



Y-cut of a CTGS crystal,  $\Lambda$ =50 µm, f=46.563 MHz



Y-cut of a CTGS crystal,  $\Lambda$ =28 µm, f=100.4186 MHz



Y-cut of a CTGS crystal,  $\Lambda$ =28 µm, f=100.4565 MHz



Y-cut of a CTGS crystal,  $\Lambda$ =28 µm, f=100.4734 MHz



## Y-cut of an LGS crystal, $\Lambda{=}50~\mu m,\,f{=}39.387~MHz$

8. Ordering Ca<sub>3</sub>TaGa<sub>3</sub>Si<sub>2</sub>O<sub>14</sub> crystal

X-ray diffraction by X-cut of a CTGS crystal modulated by SAW with wavelength of  $\Lambda$ =4 µm. E=11 keV,  $\lambda$ =1.166 Å, reflection (110),  $\Theta_{B}$ =7.7764°,  $f_{0}$ =700 MHz, V=2800 m/s



X-ray diffraction by X-cut of a CTGS crystal modulated by SAW with wavelength of  $\Lambda$ =4 µm. E=11 keV,  $\lambda$ =1.166 Å, reflection (110),  $\Theta_{B}$ =7.7764°,  $f_{0}$ =700 MHz, V=2800 m/s



Rocking curve, U=10 V



X-ray diffraction by the Y-cut of a CTGS crystal modulated by a SAW: rocking curves measured at SAW amplitudes  $h_0=0$  Å and  $h_0=8$  Å; 2D map of the distribution of the diffracted X-ray radiation on the crystal surface.  $\lambda=1.54$  Å; (200) reflection;  $\Theta_B=12.598^\circ$ ;  $f_0=693$  MHz; V=2772 m/s;  $\Lambda=4$  µm.

## X-cut of CTGS crystal



X-ray diffraction by the X-cut of a CTGS crystal modulated by a SAW: rocking curves measured at SAW amplitudes  $h_0=0$  Å and  $h_0=3$  Å; 2D map of the distribution of the diffracted X-ray radiation on the crystal surface.  $\lambda=1.54$  Å; (200) reflection;  $\Theta_B=12.598^\circ$ ;  $f_0=700$  MHz; V=2800 m/s;  $\Lambda=4$  µm.

9. Non-ordering  $La_3Ga_{5.3}Ta_{0.5}AI_{0.2}O_{14}$  crystal



X-ray penetration depth in LGTA crystal for (100), (110), and (101) reflections versus X-ray energy. Black circles show the energy of E=12.5 keV.

Y-cut of LGTA crystal: reflection(100);  $\Theta_B$ =3.990°;  $\Lambda$ =6 µm; *f*=370 MHz; V=2220 m/s.



Intensities of the diffraction satellites vs. amplitude of the input signal supplied to the IDT.





Map of the diffracted X-ray intensity at the Ycut of an LGTA modulated by SAW.  $\alpha$ =0.0°.



Rocking curves measured for different amplitudes of the input signal supplied to the IDT.

X-cut of LGTA crystal: reflection (110);  $\Theta_B = 7.030^\circ$ ;  $\Lambda = 6 \mu m$ ; f=390 MHz; V=2340 m/s.



Rocking curves measured for different amplitudes of the input signal supplied to the IDT.





Intensities of the diffraction satellites vs. amplitude of the input signal supplied to the IDT.





Map of the diffracted X-ray intensity at the Ycut of an LGTA modulated by SAW.  $\alpha$ =4.0°.



Rocking curves measured for different amplitudes of the input signal supplied to the IDT.

10. Investigation of surface and pseudo-surface acoustic waves excitation and propagation in  $La_3Ga_5SiO_{14}$  crystal



X-ray diffraction by the Z-cut of an LGS crystal modulated by a SAW (SAW propagation along (X+30°) direction): (a) dependences of the intensities of the diffraction satellites versus amplitude of the input signal supplied to the IDT; (b) rocking curves measured at amplitude of the input signal U=15 V; (c) 2D map of the distribution of the diffracted X-ray radiation on the crystal surface. (001) reflection;  $\Theta_B$ =5.619°. The resonance frequency of  $\Lambda$ =6 µm SAW excitation was *f*=416 MHz, which corresponds to SAW velocity of **V=2496 m/s**, while in the case of PSAW excitation the resonance excitation frequency is *f*=496 MHz at the velocity of **V=2976 m/s**.



X-ray diffraction by the Z-cut of an LGS crystal modulated by a SAW (SAW propagation along (X+60°) direction): (a) dependences of the intensities of the diffraction satellites versus amplitude of the input signal supplied to the IDT; (b) rocking curves measured at amplitude of the input signal U=20 V; (c) 2D map of the distribution of the diffracted X-ray radiation on the crystal surface. (001) reflection;  $\Theta_B$ =5.619°. The SAW with wavelength of  $\Lambda$ =6 µm was excited at resonance frequency *f*=396 MHz and propagated on the crystal surface with a velocity of **V=2376 m/s**. The PSAW was excited at resonance excitation frequency *f*=516 MHz and propagated with a velocity of **V=3096** m/s.



Schemes of the SAW and PSAW propagation in the Z-cut of an LGS crystal

# **Thanks for your attention!**